Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2766	((substrate or board or "printed circuit board" or pcb) and (chip or "intergrated circuit" or (semiconductor adj (chip or die)) or IC) and "heat sink" and (chamber or cavity) and (fluid or liquid or gas) and base)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:11
L2	6884	((substrate or board or "printed circuit board" or pcb) and (chip or "intergrated circuit" or (semiconductor adj (chip or die)) or IC) and "heat sink" and (chamber or cavity) and (fluid or liquid or gas) and base or "cold plate")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:23
L3	210	2 and ("power convertor" or "power module")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:15
L4	2873	((substrate or board or "printed circuit board" or pcb) and (chip or "intergrated circuit" or (semiconductor adj (chip or die)) or IC) and "heat sink" and (chamber or cavity) and (fluid or liquid or gas) and (base or "cold plate"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:23
L5	116	4 and ("power module" or "power convertor")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 12:24
S1	2085	361/700,698-699,703.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:05
S2	0	165/80.4,104.33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:05
S3	2779	165/80.4,104.33.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/10/06 06:06
S4	2011	257/714-715.cds.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:06
S 5	2085	S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:06

S6	3818	S1 S3	US-PGPUB;	OR	ON	2005/10/06 06:06
			USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S7	5009	S4 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:06
S8	2847	S7 and (power module)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:07
S9	267	S8 and vapor same chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:08
S10	10	("4019098" "4327399" "4519447" "4727455" "4833567" "4880053" "5199165" "5216580" "5769154" "6056044").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/10/06 06:17
S11	1	("6483705").URPN.	USPAT	OR	OFF	2005/10/06 06:21
S12	81	S8 and vapor adj chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:25
S13	6034524	die or chip or semiconductor die or semiconductor chip or intergrated circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:32
S14	6871839	substrate or board or printed circuit board or pcb	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:30
S15	3515636	heat sink	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:31
S16	2769820	chamber or cavity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 06:33
S17	801535	condens\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/10/06 06:33

Same S14 same S15 same S16							
S20 S583 S19 and (fluid liquid gas) S19 and (fluid liquid gas) USPAT; USCR; EPC); IPC) DERWENT; IBIN_TOB USPAT; USCR; EPC); IPC);	S18	45920	S13 same S14 same S15 same S16	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:36
S21 2646 S20 and seal\$3 S20 S20 and seal\$3 S20 S20 S20 and seal\$3 S20 S20	S19	6377	S17 same S18	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:36
USPAT; USOCR; EPO; IPO; DERWENT; IBM_TDB US-RGPUB; USPAT; USOCR; EPO; IPO; DERWENT; ISOCR US-RGPUB; USPAT; USOCR; EPO; IPO; USPAT; USOCR US-RGPUB; USPAT; USOCR USPAT; USO	S20	5583	S19 and (fluid liquid gas)	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:37
S23 2710 S7 and (chamber cavity well) USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB USPAT; USOCR;	S21	2646	S20 and seal\$3	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:40
USPAT; USOCR; PO; PO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR; PO; PO; PO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR; PO; PO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR US-PGPUB; USPAT; USOCR US-PGPUB; USPAT; USOCR USPAT;	S22	2673	S20 and (power module semiconductor power module invertor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:47
S25 921 (361/699).CCLS. US-PAT; USOCR; EPO; JPO; DERWENT; IBM_TDB OR US-PAT; USOCR; EPO; JPO; DERWENT; IBM_TDB OR US-PAT; USOCR; EPO; JPO; DERWENT; IBM_TDB OR US-PGPUB; OR US-PGPUB; USPAT; USOCR US-PGPUB; US-PGPU	523		S7 and (chamber cavity well)	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 06:50
S26 5 ("5262921" "5349498" "5455458" "5666269" US-PGPUB; US-PGPU	524	951	S23 and condens\$3	USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/10/06 07:03
"5978220").PN. USPAT; USOCR USPAT; USOCR USPAT OR OFF 2005/10/06 07:25	S25	921	(361/699).CCLS.	USPAT; USOCR; EPO; JPO; DERWENT;	OR	OFF	2005/10/06 07:03
528 4 ("4323914" "4335781" "5185194" "5243223").PN. US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:29 529 28 ("5455458").URPN. USPAT OR OFF 2005/10/06 07:30 530 7 ("3788393" "4652970" "4782893" "4805691" "5043845" USPAT; USOCR US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:42 531 1 ("4494171").PN. US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:45	S26	5		USPAT;	OR	OFF	2005/10/06 07:24
528 4 ("4323914" "4335781" "5185194" "5243223").PN. US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:29 529 28 ("5455458").URPN. USPAT OR USPAT OR OFF 2005/10/06 07:30 530 7 ("3788393" "4652970" "4782893" "4805691" "5043845" USPAT; USOCR US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:42 531 1 ("4494171").PN. US-PGPUB; USPAT; USOCR OR OFF 2005/10/06 07:45	S27	1	("6473303").URPN.	USPAT	OR	OFF	2005/10/06 07:25
S29 28 ("5455458").URPN. USPAT; USOCR USPAT OR OFF 2005/10/06 07:30							1 .
S30 7 ("3788393" "4652970" "4782893" "4805691" "5043845" US-PGPUB; USPAT; USOCR USPAT; USOCR	520	1	(15252. 1555/52 5255251 5215225).114.	USPAT;			2003, 10,00 07.23
S31 1 ("4494171").PN. US-PGPUB; US-PGPUB; USPAT; USOCR US-PGPUB; USPAT; USOCR US-PGPUB; USPAT; USOCR USPAT; USOCR	529	28	("5455458").URPN.	USPAT	OR	OFF	2005/10/06 07:30
USPAT; USOCR	S30	7		USPAT;	OR	OFF	2005/10/06 07:42
S32 18 ("5316075").URPN. USPAT OR OFF 2005/10/06 07:54	S31	1	("4494171").PN.	USPAT;	OR	OFF	2005/10/06 07:45
	532	18	("5316075").URPN.	USPAT	OR	OFF	2005/10/06 07:54

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S33	889	(361/700).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:11
S34	168	(361/698).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:15
S35	358	(361/703).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:24
S36	1281	(165/80.4).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:24
S 37	13	("2695753" "4019098" "4106557" "4327399" "4635709" "4949164" "5057909" "5131233" "5168919" "5305184" "5316077" "5413965").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/10/06 08:33
538	14	("5508884").URPN.	USPAT	OR	OFF	2005/10/06 08:33
S39	1	("3673306").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/10/06 08:38
S40	26	("4047198").URPN.	USPAT	OR	OFF	2005/10/06 08:40
S41	2346	165/104.33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:40
S42	11	("4279292" "4326843" "4612978" "4758927" "5130498" "5213877" "5451279" "5473510" "5675474" "5926371" "5959840").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/10/06 08:53
543	2	("6483185").URPN.	USPAT	OR	OFF	2005/10/06 09:17
S44	18	257/714-715	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 09:18
S45	2011	(257/714-715).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 09:28
S46	34	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3).clm.	US-PGPUB	OR	ON	2005/10/06 10:03
S47	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3 and seal and "metal form").clm.	US-PGPUB	OR	ON	2005/10/06 09:46

S48	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3 and seal and "metal foam").clm.	US-PGPUB	OR	ON	2005/10/06 09:47
549	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3 and seal and "metal foam").clm.	US-PGPUB	OR	ON	2005/10/06 09:47
S50	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3 and seal and foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:48
S51	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condens\$3 and seal and foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:48
S52	0	(substrate and board and pcb and "circuit board" and die and chip and "intergrated circuit" and "semiconductor die" and IC and heat sink and (chamber or cavity) and vapor and condensing and seal and foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:49
S53	20632	(substrate and board and pcb and circuit board and die and chip and intergraded circuit and semiconductor die and IC and heat sink and (chamber or cavity) and vapor and condensing and seal and foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:55
S54	31872	(substrate and board and pcb and circuit board and die and chip and intergraded circuit and semiconductor die and IC and heat sink and (chamber or cavity) and vapor and condensing and seal and metal foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:56
S55	31872	(substrate and board and pcb and circuit board and die and chip and intergraded circuit and semiconductor die and IC and heat sink and(chamber or cavity)and vapor and condensing and seal and metal foam).clm.	US-PGPUB	OR -	ON	2005/10/06 09:56
S56	11282	(substrate and board and pcb and "circuit board" and die and chip and "intergraded circuit" and "semiconductor die" and IC and heat adj sink and(chamber or cavity)and vapor and condensing and seal and metal foam).clm.	US-PGPUB	OR	ON	2005/10/06 09:58
S57	9	substrate and "semiconductor die" and "heat sink" and chamber and condens\$3.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:06
S58	3	substrate and "semiconductor die" and "heat sink" and chamber and fluid and base and condens\$3.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:07
S59	3187393	(substrate or board or "printed circuit board" or "wiring board" or pcb and (chip or "intergrated circuit" or "semiconductor die" or IC "semicoductor chip") and "heat sink" and (chamber or cavity) and (fluid or liquid or gas) and base)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:54
S60	712774	S59 and (power module or invertor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:44

S61	8549	S59 and ("power module" or invertor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:46
S62	1190322	S59 and power module	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:47
S63	5706	S59 and "power module"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:55